

# XP231N0201TR-G

N-channel MOSFET 30V, 0.2A

ETR11041-001a

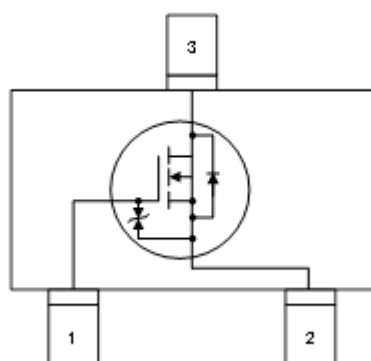
## FEATURES

On-State Resistance :  $R_{DS(on)}=5.0\Omega @V_{GS}=4.5V$   
 Driving voltage : 2.5V  
 Environmentally Friendly : EU RoHS Compliant, Pb Free

## APPLICATIONS

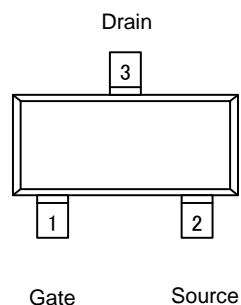
● Switching

## EQUIVALENT CIRCUIT



## PIN CONFIGURATION

● SOT-23(TO-236)



## PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT
XP231N0201TR-G *	SOT-23(TO-236)	3,000 pcs/ Reel

\* The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant

## ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±20	V
Drain Current (DC)	$I_D$	0.2	A
Drain Current(Pulse) <sup>(*)</sup>	$I_{DP}$	0.4	A
Channel Power Dissipation <sup>(**)</sup>	$P_d$	0.4	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C

<sup>(\*)</sup> $PW \leq 10\mu s$ , duty cycle  $\leq 1\%$

<sup>(\*\*)</sup>When implemented on a PCB defined by JESD51-7

## ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	30	-	-	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(off)}$	$I_D = 250\mu A, V_{DS} = V_{GS}$	0.8	1.3	1.8	V
Drain-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 10mA$	-	3	5	$\Omega$
		$V_{GS} = 2.5V, I_D = 10mA$	-	5.5	11	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	-	6.5	-	pF
Output Capacitance	$C_{oss}$		-	2.5	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	1.2	-	pF
Turn-on Delay Time	$t_{d(on)}$		-	7	-	ns
Rise Time	$t_r$	$V_{DD} = 10V, I_D = 100mA$ $V_{GS} = 10V$	-	5	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	20	-	ns
Fall Time	$t_f$		-	8	-	ns
Total Gate Charge	$Q_g$		$V_{DS} = 10V, I_D = 100mA$ $V_{GS} = 10V$	-	0.18	-
Gate-Source Charge	$Q_{gs}$	-		0.03	-	nC
Gate-Drain Charge	$Q_{gd}$	-		0.08	-	nC
Diode Forward Voltage	$V_{SD}$	$I_S = 100mA, V_{GS} = 0V$	-	0.8	1.2	V

## NOTES ON USE

1. Please use this IC within the absolute maximum ratings.

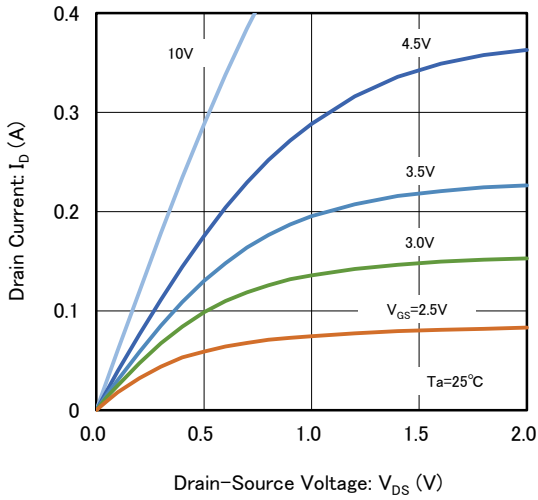
Even within the ratings, in case of high load use continuously such as high temperature, high voltage, high current and thermal stress may cause reliability degradation of the IC.

2. Torex places an importance on improving our products and their reliability.

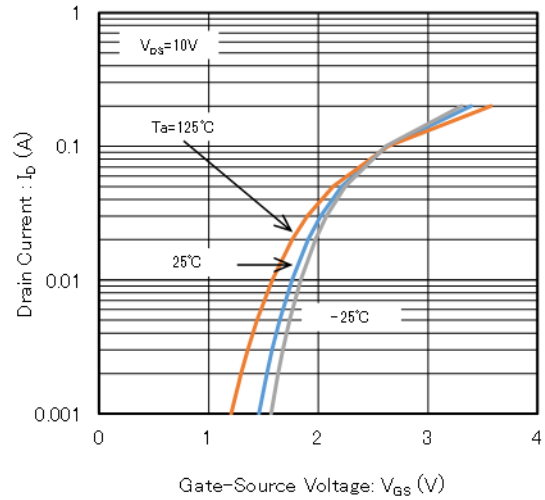
We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

# TYPICAL PERFORMANCE CHARACTERISTICS

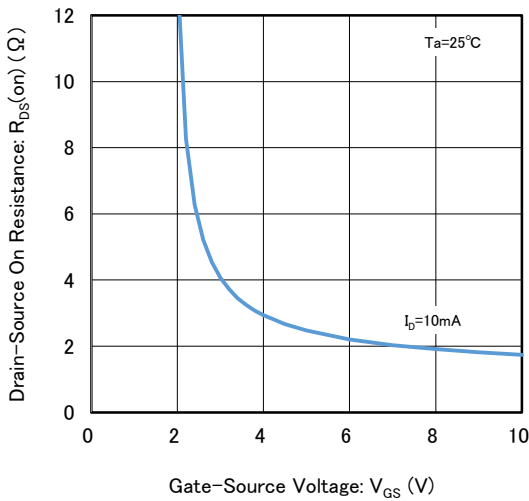
(1) Drain Current vs. Drain-Source Voltage



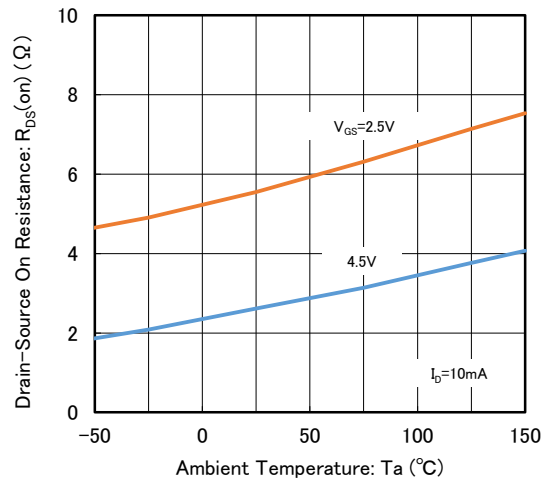
(2) Drain Current vs. Gate-Source Voltage



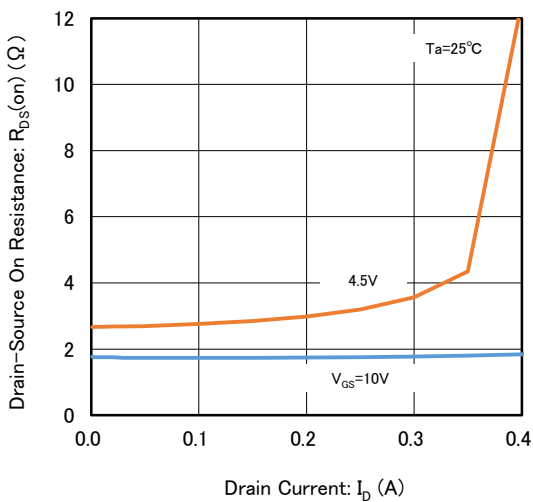
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



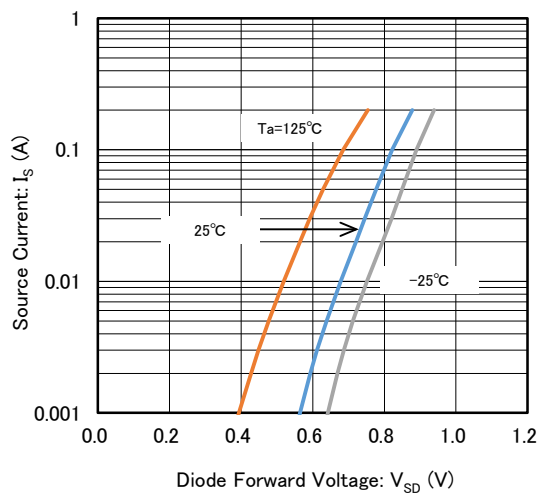
(4) Drain-Source On-State Resistance vs. Ambient Temperature



(5) Drain-Source On-State Resistance vs. Drain Current

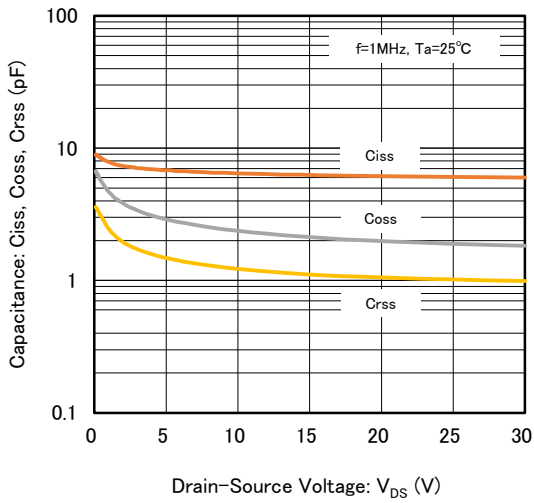


(6) Source Current vs. Diode Forward Voltage

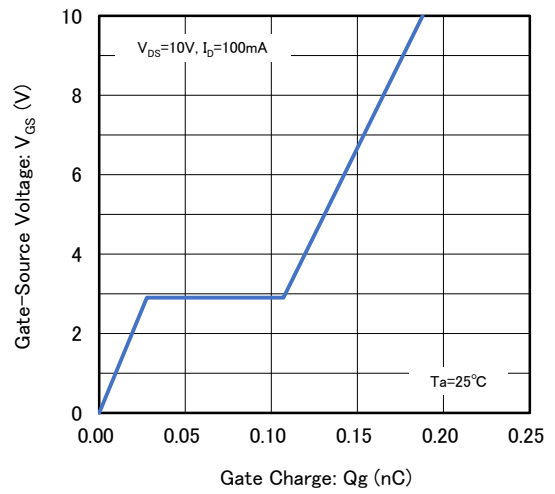


## TYPICAL PERFORMANCE CHARACTERISTICS

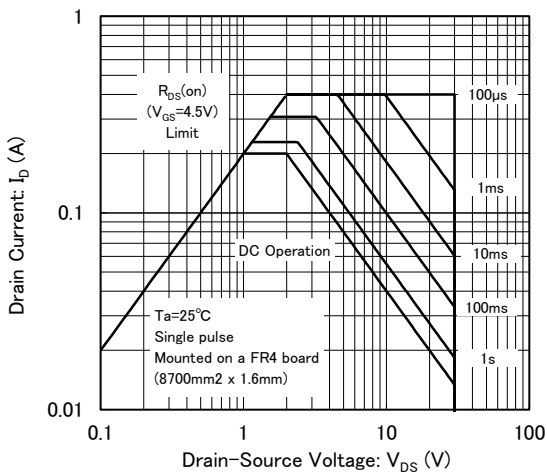
(7)  $C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$  vs. Drain-Source Voltage



(8) Gate-Source Voltage vs. Gate Charge



(9) Area of Safe Operation



## ■ PACKAGING INFORMATION

For the latest package information go to, [www.torexsemi.com/technical-support/packages](http://www.torexsemi.com/technical-support/packages)

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS	
SOT-23(TO-236)	<a href="#">SOT-23(TO-236) PKG</a>	JESD51-7 Board	<a href="#">SOT-23(TO-236) PowerDissipation</a>

## ■ MARKING RULE

### ● SOT-23(TO-236)

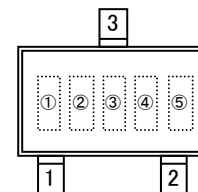
① ② ③ represents product series

MARK			PRODUCT SERIES
①	②	③	
3	1	N	XP231N0201**-G

④, ⑤ represents production lot number  
 01 to 09, 0A to 0Z, 11 to 9Z, A1 to A9, AA to AZ, B1 to ZZ repeated  
 (G, I, J, O, Q, W excluded)

\*No character inversion used

SOT-23(TO-236)



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